

IN THE CLAIMS:

Please cancel claims 2-3, 8, 10-11, 16 and 22-29 without prejudice, and amend the claims as follows:

1. (Currently Amended) A thermal shim adapted to be positioned between a wafer retention device and a pedestal, wherein said thermal shim comprises a disk having a central region circumscribed by an outer region, wherein the central region is made of a first a thermally insulative material and the outer region is made of a second centrally located within a thermally conductive material.
2. (Canceled)
3. (Canceled)
4. (Currently Amended) The thermal shim of claim 1, wherein ~~said thermally conductive material~~ the outer region is in the shape of an annulus.
5. (Currently Amended) The thermal shim of claim 1, wherein the ~~thermally conductive material~~ the outer region is fabricated of a metallic material.
6. (Original) The thermal shim of claim 5 wherein said metallic material is aluminum or copper.
7. (Original) The thermal shim of claim 1 wherein the thermal shim is fabricated of a corrugated material.
8. (Canceled)
9. (Currently Amended) A wafer support comprising:
a heat exchanger pedestal having a top surface;

a thermal shim comprising a disk having a central region circumscribed by an outer region, wherein the central region is made of a thermally insulative first material and the outer region is made of a centrally disposed within a thermally conductive second material; and

a wafer retention device having a bottom surface, wherein the thermal shim is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.

10. (Canceled)

11. (Canceled)

12. (Currently Amended) The wafer support of claim 9, wherein ~~said thermally conductive material~~ the outer region is in the shape of an annulus.

13. (Currently Amended) The wafer support of claim 9, wherein the ~~thermally conductive material~~ outer region is fabricated of a metallic material.

14. (Original) The wafer support of claim 13 wherein said metallic material is aluminum or copper.

15. (Original) The wafer support of claim 9 wherein the thermal shim is fabricated of a corrugated material.

16. (Canceled)

17. (Currently Amended) An etch reactor having a wafer support, wherein said wafer support comprises:

a heat exchanger pedestal having a top surface;

a thermal shim comprising a disk having a central region circumscribed by an outer region, wherein the central region is made of a thermally insulative first material

~~centrally disposed within an annular shaped~~ and the outer region is made of a second thermally conductive material; and

an electrostatic chuck having a bottom surface, wherein the thermal shim is located between the bottom surface of the electrostatic chuck and the top surface of the heat exchanger pedestal.

18. (Previously Presented) The etch reactor of claim 1, wherein the thermal shim is fabricated of metal.

19. (Previously Presented) The etch reactor of claim 1, wherein the thermal shim is corrugated.

20. (Currently Amended) A wafer support comprising:
a heat exchanger pedestal having a top surface;
~~means for controlling thermal conductivity having a thermally insulative material centrally disposed within a thermally conductive material; and~~
a wafer retention device having a bottom surface, ~~wherein the means for controlling thermal conductivity is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal; and~~
means for controlling thermal conductivity between the heat exchanger and the wafer retention device, wherein the controlling means is disposed between the top surface of the heat exchanger pedestal and the bottom surface of the wafer retention device.

21. (Currently Amended) The wafer support of claim 20 wherein said means for controlling the thermal conductivity is a thermal shim comprising a disk having a central region circumscribed by an outer region, wherein the central region is made of a first material and the outer region is made of a second material.

22-29. (Cancelled)

Please add the following new claims:

30. (New) The thermal shim of claim 1, wherein the disk substantially covers a top surface of the pedestal.

31. (New) The thermal shim of claim 1, wherein the central region is made of a thermally insulative material and the outer region is made of a thermally conductive material.

32. (New) The thermal shim of claim 1, wherein the central region is made of a thermally conductive material and the outer region is made of a thermally insulative material.

33. (New) The wafer support of claim 9, wherein the disk substantially covers a top surface of the pedestal.

34. (New) The wafer support of claim 9, wherein the central region is made of a thermally insulative material and the outer region is made of a thermally conductive material.

35. (New) The wafer support of claim 9, wherein the central region is made of a thermally conductive material and the outer region is made of a thermally insulative material.

36. (New) The wafer support of claim 9, wherein the central region is a hole.

37. (New) The etch reactor of claim 17, wherein the disk substantially covers a top surface of the pedestal.

38. (New) The etch reactor of claim 17, wherein the central region is made of a thermally insulative material and the outer region is made of a thermally conductive material.
39. (New) The etch reactor of claim 17, wherein the central region is made of a thermally conductive material and the outer region is made of a thermally insulative material.
40. (New) The etch reactor of claim 17, wherein the central region is a hole.
41. (New) A wafer support comprising:
a heat exchanger pedestal having a top surface;
a wafer retention device having a bottom surface;
a thermal shim disposed between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal, wherein the thermal shim comprises a disk having a central region circumscribed by an outer region, wherein the central region forms an air gap between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.
42. (New) The wafer support of claim 41, wherein the central region is a hole.
43. (New) The wafer support of claim 41, wherein the outer region is made of a thermally conductive material.
44. (New) The wafer support of claim 41, wherein the air gap transfers less heat to the heat exchanger pedestal than the outer region.
45. (New) An etch reactor having a wafer support, wherein said wafer support comprises:
a heat exchanger pedestal having a top surface;
a wafer retention device having a bottom surface;

a thermal shim disposed between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal, wherein the thermal shim comprises a disk having a central region circumscribed by an outer region, wherein the central region forms an air gap between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.

- 46. (New) The wafer support of claim 45, wherein the central region is a hole.
- 47. (New) The wafer support of claim 45, wherein the outer region is made of a thermally conductive material.
- 48. (New) The wafer support of claim 45, wherein the air gap transfers less heat to the heat exchanger pedestal than the outer region.